

## ISL9R1560PF2

## 15A, 600V Stealth™ Diode

### **General Description**

The ISL9R1560PF2 is a Stealth™ diode optimized for low loss performance in high frequency hard switched applications. The Stealth™ family exhibits low reverse recovery current (I<sub>RM(REC)</sub>) and exceptionally soft recovery under typical operating conditions.

This device is intended for use as a free wheeling or boost diode in power supplies and other power switching applications. The low  $I_{RM(REC)}$  and short  $t_a$  phase reduce loss in switching transistors. The soft recovery minimizes ringing, expanding the range of conditions under which the diode may be operated without the use of additional snubber circuitry. Consider using the Stealth  $^{\text{TM}}$  diode with an SMPS IGBT to provide the most efficient and highest power density design at lower cost.

Formerly developmental type TA49410.

#### **Features**

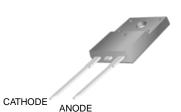
•	Soft Recovery $t_b/t_a > 1.2$
•	Fast Recovery $t_{rr}$ < 30ns
•	Operating Temperature
•	Reverse Voltage 600V
•	Internally Isolated 1kV

### · Avalanche Energy Rated

### **Applications**

- Switch Mode Power Supplies
- · Hard Switched PFC Boost Diode
- · UPS Free Wheeling Diode
- Motor Drive FWD
- SMPS FWD
- · Snubber Diode

# Package Symbol



TO-220F

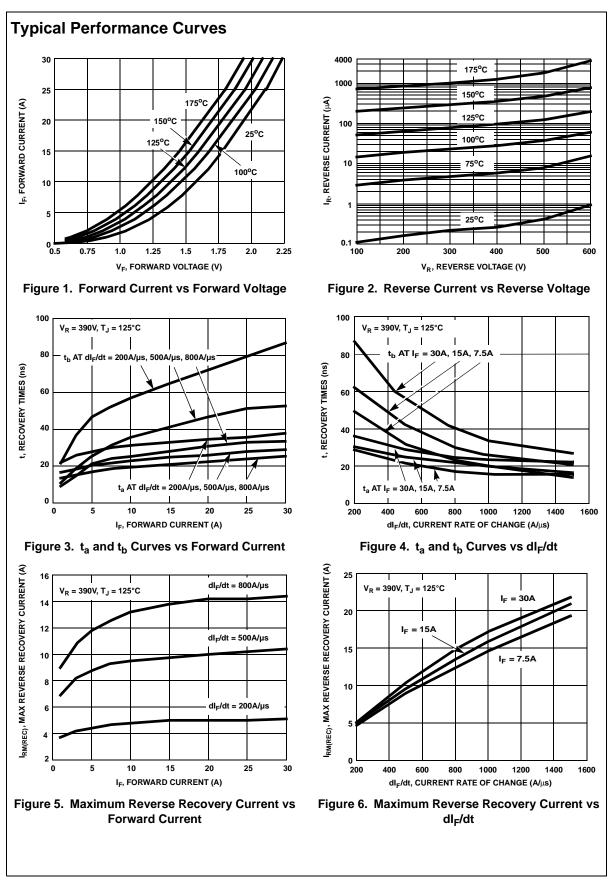


# Device Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

$\begin{array}{c ccccccccccccccccccccccccccccccccccc$
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$
I <sub>F(AV)</sub> Average Rectified Forward Current (T <sub>C</sub> = 25°C)     15     A       I <sub>FRM</sub> Repetitive Peak Surge Current (20kHz Square Wave)     30     A       I <sub>FSM</sub> Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60Hz)     200     A
IFRM     Repetitive Peak Surge Current (20kHz Square Wave)     30     A       IFSM     Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60Hz)     200     A
I <sub>FSM</sub> Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60Hz) 200 A
Tom 1
Po Power Dissipation 30 W
. D   1 010 2 00   1
E <sub>AVL</sub> Avalanche Energy (1A, 40mH) 20 mJ
T <sub>J</sub> , T <sub>STG</sub> Operating and Storage Temperature Range -55 to 150 °C
T <sub>L</sub> Maximum Temperature for Soldering
Leads at 0.063in (1.6mm) from Case for 10s 300 °C

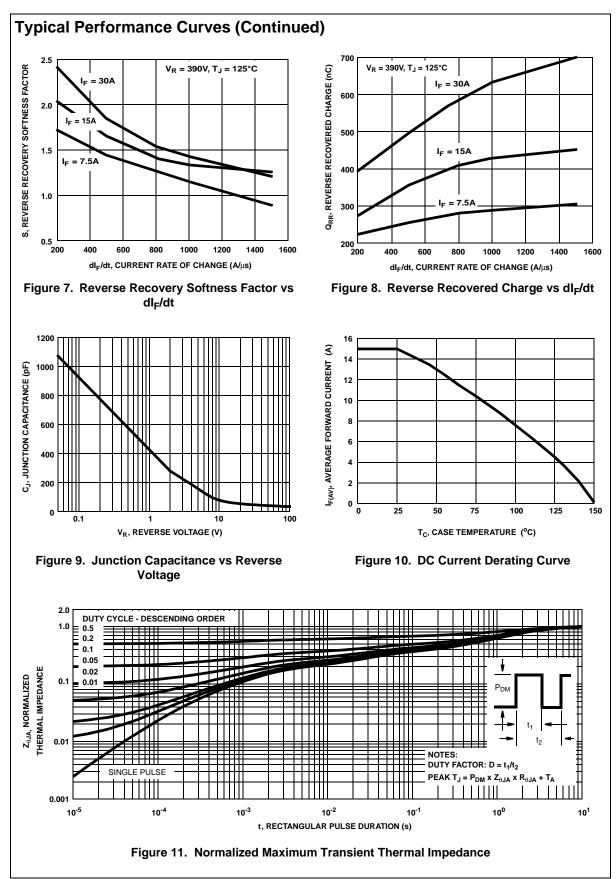
CAUTION: Stresses above those listed in "Device Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

lectrica Symbol			Package	Tape Width			Quar	itity
Symbol ff State	al Char	Device Marking Device R1560PF2 ISL9R1560PF2		N/A			50	
		acteristics т <sub>с = 25°</sub> с	C unless otherwise	e noted				
		Parameter	Test	Conditions	Min	Тур	Max	Uni
I <sub>R</sub>	Characte	eristics						
	Instantaneo	ous Reverse Current	V <sub>R</sub> = 600V	T <sub>C</sub> = 25°C	-	-	100	μΑ
				T <sub>C</sub> = 125°C	-	-	1.0	m/
n State	Characte	eristics						
V <sub>F</sub>	Instantaneo	ous Forward Voltage	I <sub>F</sub> = 15A	T <sub>C</sub> = 25°C	-	1.8	2.2	V
				$T_C = 125^{\circ}C$	-	1.65	2.0	V
ynamic	Characte	eristics						
C <sub>J</sub> .	Junction Ca	apacitance	$V_R = 10V, I_F = 0$	)A	-	62	-	pF
witching	g Charact	tarietice						
		ecovery Time	1 - 10 dl /dt -	- 1004/up 1/ - 201/	_	25	20	nc
t <sub>rr</sub>	Reverse Re	ecovery rime		= $100A/\mu s$ , $V_R = 30V$ = $100A/\mu s$ , $V_R = 30V$		25 35	30 40	ns
+	Povorco Po	ecovery Time	$I_{F} = 15A, dI_{F}/dI$	$= 100 \text{A/}\mu\text{S}, \text{ V}_{\text{R}} = 30 \text{ V}$		29.4	-	ns
			$dI_F = 15A$ , $dI_F / dt = 200A / \mu$	s		3.5	-	ns A
-		Reverse Recovery Current	$V_R = 390V, T_C = 1000$			57		nC
		ecovered Charge						
		ecovery Time	$I_F = 15A,$ $dI_F/dt = 200A/\mu$	c	-	90	-	ns
	Softness Fa		$V_R = 390V$	5,	-	2.0	-	<u> </u>
IRM(REC) IVIAXIIIIUIII Reverse Recovery Current			$T_{\rm C} = 125^{\circ}{\rm C}$		-	5.0	-	Α
	Reverse Recovered Charge				-	275 52	-	nC
			·	I <sub>F</sub> = 15A, dI <sub>F</sub> /dt = 800A/μs,			-	ns
_							-	
\ -/	10 = 1/5%				-	13.5	-	Α
	Reverse Recovered Charge			-	390	-	nC	
dI <sub>M</sub> /dt Maximum di/dt during t <sub>b</sub> - 80				800	-	A/µ		
hermal C	Characte	ristics						
000		esistance Junction to Case			-	-	4.1	°C/\
$R_{\theta JA}$	Thermal Re	esistance Junction to Ambie	ent TO-247		-	-	70	°C/\



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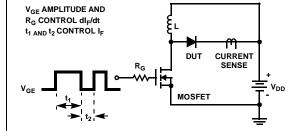
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# **Test Circuit and Waveforms**



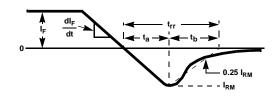
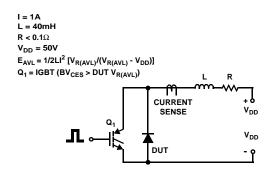


Figure 12. t<sub>rr</sub> Test Circuit

Figure 13. t<sub>rr</sub> Waveforms and Definitions



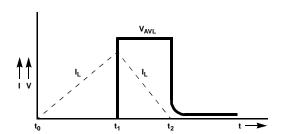


Figure 14. Avalanche Energy Test Circuit

Figure 15. Avalanche Current and Voltage Waveforms

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Bottomless™ FAS <sup>™</sup>	ST®	LittleFET™	Power247™	SuperSOT™-3
CoolFET™ FAS	STr™	MicroFET™	PowerTrench®	SuperSOT™-6
CROSSVOLT™ FRF	ET™	MicroPak™	QFET™	SuperSOT™-8
DOME™ Glob	oalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™ GTO	Отм .	MSX™	QT Optoelectronics™	TinyLogic <sup>®</sup>
E <sup>2</sup> CMOS™ HiSe	еС™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™ I2C™	М	OCX <sup>TM</sup>	RapidConfigure™	UHC™
Across the board. Arou	und the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franchise™	M	OPTOLOGIC®	SILENT SWITCHER®	VCX™
Programmable Active D	Droop™	OPTOPLANAR™	SMART START™	

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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

### PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

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Rev. I2